Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
Tech ID: 25014 / UC Case 2004-495-0

BRIEF DESCRIPTION
A method for fabricating high-quality indium-containing epitaxial layers, heterostructures, and devices based on InGaN growth on GaN substrates.

BACKGROUND
GaN and its alloys (AlGaN, InGaN, AlInGaN) have been established as effective for fabrication of visible and ultraviolet optoelectronic devices and high-power electronic devices. These devices are most often grown along the polar c-direction, using a variety of growth techniques, including molecular beam epitaxy (MBE), metalorganic chemical vapor deposition (MOCVD), or hydride vapor phase epitaxy (HVPE). Growing devices in the polar c-direction results in charge separation, spontaneous polarization, and degraded device performance. Growth of such devices along a nonpolar axis could significantly improve their performance, but InGaN-based devices have previously encountered problems with growth conditions and material quality.

DESCRIPTION
UC Santa Barbara researchers have developed a method for fabricating high-quality indium-containing epitaxial layers, heterostructures, and devices based on InGaN growth on GaN substrates. These InGaN films are grown along the nonpolar direction using a metalorganic chemical vapor deposition technique, and result in the successful creation of violet and near-ultraviolet LEDs and LDs. Previous issues related to the growth of InGaN-based devices, such as gross surface roughening, low indium incorporation, and indium desorption in InGaN heterostructures have been overcome with this technique.

ADVANTAGES
- Variability in layer thickness
- Violet and near-ultraviolet light emission
- Growth of nonpolar InGaN at a reduced temperature
- Growth of InGaN layers at or near atmospheric pressure

APPLICATIONS
- LEDs
- Laser diodes (LDs)

PATENT STATUS

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<td>United States Of America</td>
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<td>8,502,246</td>
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<td>7,186,302</td>
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OTHER INFORMATION

KEYWORDS
indssl, indled, GaN, thin films

CATEGORIZED AS
- Energy
- Lighting
- Semiconductors
- Design and Fabrication

RELATED CASES
2004-495-0
Enhanced Optical Polarization of Nitride LEDs by Increased Indium Incorporation
- Lateral Growth Method for Defect Reduction of Semipolar Nitride Films
- Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- III-Nitride-Based Devices Grown With Relaxed Active Region
- Achieving "Active P-Type Layer/Layers" In III-Nitride Epitaxial Or Device Structures Having Buried P-Type Layers
- High-Quality N-Face GaN, InN, AIN by MOCVD
- Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs (UC Case 2010-183)
- Defect Reduction in GaN films using in-situ SiNx Nanomask
- Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- Group III Nitride-Based High Electron Mobility Transistor (Hermt) With Barrier/Space Layer
- Highly Efficient Blue-Violet III-Nitride Semipolar Laser Diodes
- Hybrid Growth Method for Improved III-Nitride Tunnel Junction Devices
- Low Temperature Deposition of Magnesium Doped Nitride Films
- Transparent Mirrorless (TML) LEDs
- Improved GaN Substrates Prepared with Ammonothermal Growth
- Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
- Size-Independent Forward Voltage Micro-LED with an Epitaxial Junction
- A Structure For Increasing Mobility In A High-Electron-Mobility Transistor
- Method for Enhancing Growth of Semipolar Nitride Devices
- III-Nitride Tunnel Junction with Modified Interface
- Growth of Polyhedron-Shaped Gallium Nitride Bulk Crystals
- Nonpolar III-Nitride LEDs With Long Wavelength Emission
- Fabrication of Relaxed Semiconductor Films without Crystal Defects
- Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
- Methods for Locally Changing the Electric Field Distribution in Electron Devices
- Increased Light Extraction with Multistep Deposition of ZnO on GaN
- Method for Manufacturing Improved III-Nitride LEDs and Laser Diodes: Monolithic Integration of Optically Pumped and Electrically Injected III-Nitride LEDs
- Selective-Area Mesoporous Semiconductors And Devices For Optoelectronic And Photonic Applications
- High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
- Method for Growing High-Quality Group III-Nitride Crystals
- Controlled Photoelectrochemical (PEC) Etching by Modification of Local Electrochemical Potential of Semiconductor Structure
- Oxyfluoride Phosphors for Use in White Light LEDs
- Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- Thermally Stable, Laser-Driven White Lighting Device
- MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride
- Reduced Dislocation Density of Non-Polar GaN Grown by Hydride Vapor Phase Epitaxy
- Highly Compact, High-Index Dielectric Nanostructures for Deep-Ultraviolet Devices
- Reduction in Leakage Current and Increase in Efficiency of III-Nitride MicroLEDs
- GaN-based Vertical Metal Oxide Semiconductor and Junction Field Effect Transistors
- Methods for Fabricating III-Nitride Tunnel Junction Devices
- Low-Droop LED Structure on GaN Semi-polar Substrates
- Contact Architectures for Tunnel Junction Devices
- Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
- Photoelectrochemical Etching Of P-Type Semiconductor Heterostructures
- Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
- III-Nitride-Based Devices Grown On Thin Template On Thermally Decomposed Material
- Growth of Semipolar III-V Nitride Films with Lower Defect Density
- III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- Novel Current-Blocking Layer in High-Power Current Aperture Vertical Electron Transistors (CAVETs)
- Improved Manufacturing of Solid State Lasers via Patternning of Photonic Crystals
- II-N Transistor With Stepped Cap Layers
- High Efficiency III-Nitride Devices with Smooth Relaxed InGaN Buffer and Strain Compliant Template
- Tunable White Light Based on Polarization-Sensitive LEDs
- Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
- Growth of High-Performance M-plane GaN Optical Devices
- Packaging Technique for the Fabrication of Polarized Light Emitting Diodes
- Improved Anisotropic Strain Control in Semipolar Nitride Devices
- High Light Extraction Efficiency III-Nitride LED
- III-V Nitride Device Structures on Patterned Substrates
- Activation of P-Type Layers of Tunnel Junctions in Micro-LEDs
- Method for Increasing GaN Substrate Area in Nitride Devices
- Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- Growth of Planar, Non-Polar, A-Plane GaN by Hydride Vapor Phase Epitaxy
- GaN-Based Thermoelectric Device for Micro-Power Generation
- Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patterning
- LED Device Structures with Minimized Light Re-Absorption
- Growth of Planar Semi-Polar Gallium Nitride
- Nonpolar (Al, B, In, Ga)N Quantum Well Design
- UV Optoelectronic Devices Based on Nonpolar and Semi-polar AlInN and AlInGaN Alloys
- Defect Reduction of Non-Polar and Semi-Polar III-Nitrides
- III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture
- Enhancing Growth of Semipolar (Al,In,Ga,B)N Films via MOCVD
- III-N Based Material Structures and Circuit Modules Based on Strain Management